
FMD_QNC_amps_filled

Release 0.1

oliver munz

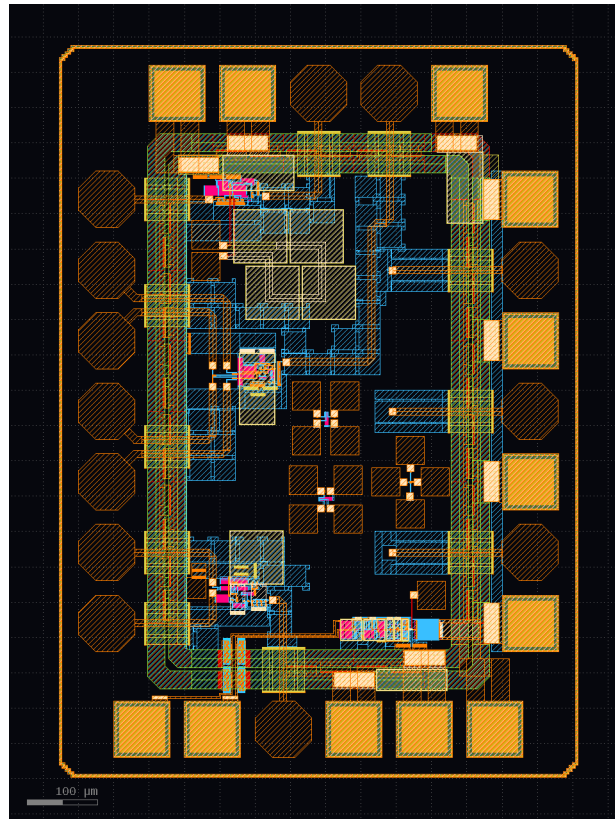
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CONTENTS

1	specifications	3
1.1	pinout	4
1.2	signals	4
2	amplifier	5
2.1	schematic	5
2.2	layout	6
3	differential amplifier	7
3.1	schematic	7
3.2	layout	8
4	dual input differential amplifier	9
4.1	schematic	9
4.2	layout	10
5	amplifier simulations	11
6	shunt regulator 3.3V	13
6.1	schematic	13
6.2	layout	14
6.3	options	14
6.4	simulation	14
7	high voltage OTA	15
7.1	OTA	15
7.2	bias generator	16
7.3	layout	17
7.4	simulations	17
7.5	ETHZ feedback	18
8	experiments	19
8.1	RPPD	19
8.2	sg13g2	19
8.3	calibration kit	19
9	design data and design process description	21
9.1	iHP 130nm BiCMOS process sg13g2	21
9.2	Xschem schematics:	21
9.3	KLAYOUT .GDS:	21

Warning

this chip is designed without correct LVS. only parts are really verified...



SPECIFICATIONS

there are 3 different amplifiers, a voltage-regulator and some experiments

1. **single ended lowpower amplifier**

- 3.3V power supply
- < 3.5mA current including powering of a laser-diode
- > 30dB gain at 1GHz
- 0..60°C
- low-pass corner programmable via capacitor

2. **dual input differential lowpower amplifier**

- 3.3V power supply
- < 3.5mA current including powering of a laser-diode
- > 10dB gain at 1GHz
- 0..60°C

3. **differential lowpower amplifier**

- 3.3V power supply
- < 3.5mA current including powering of a laser-diode
- 0dB gain at 1GHz
- 0..60°C

4. **shunt-regulator 3.3V**

- max. 50mA
- $\Delta T_c = 0$ @ 10..30°C
- trimmable
- possibility for lowpass filter

5. **test-structure for RPPD matching**

- see differences in x and y build resistors, does it really matter?
- see differences in middle and edge resistors, do we need dummy resistors?

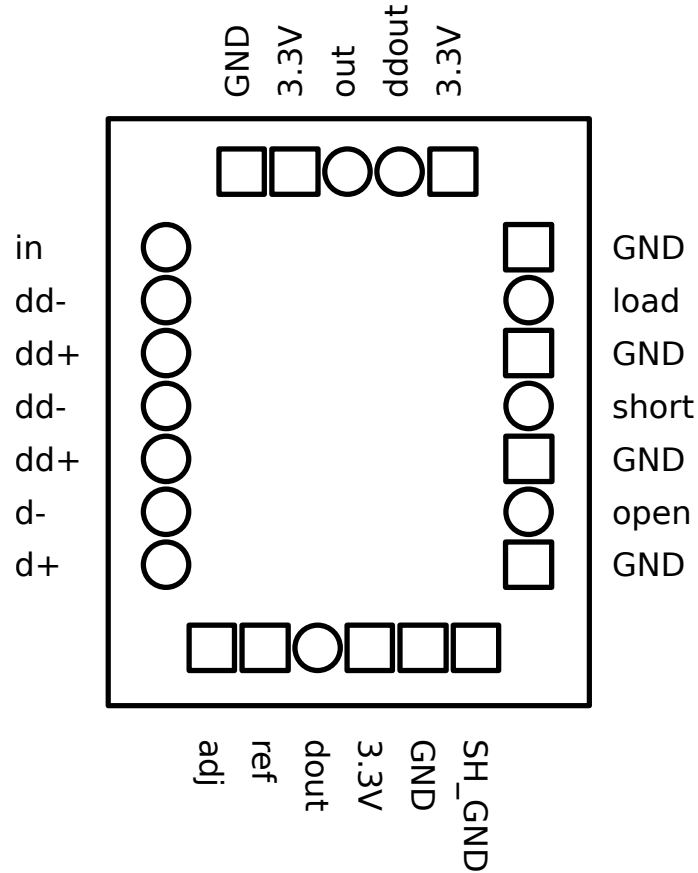
6. **a sg13g2 transistor**

- if nothing else is working, we get at least a transistor :)

7. open, short & load

- to calibrate the pads and connections out, and measure the impedances of the amplifiers

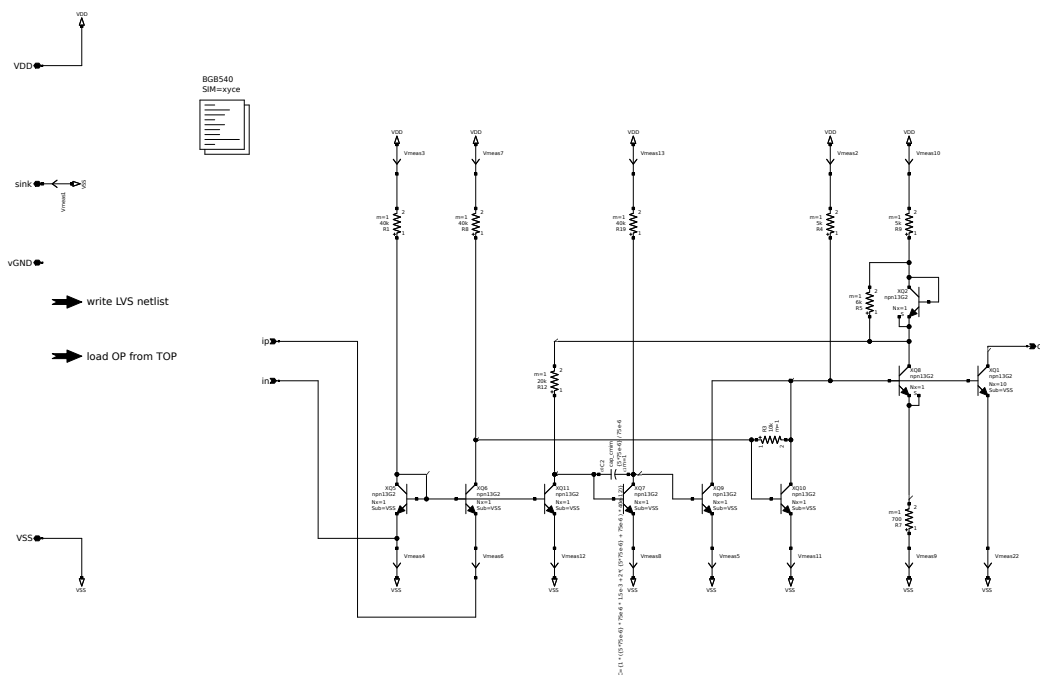
1.1 pinout



1.2 signals

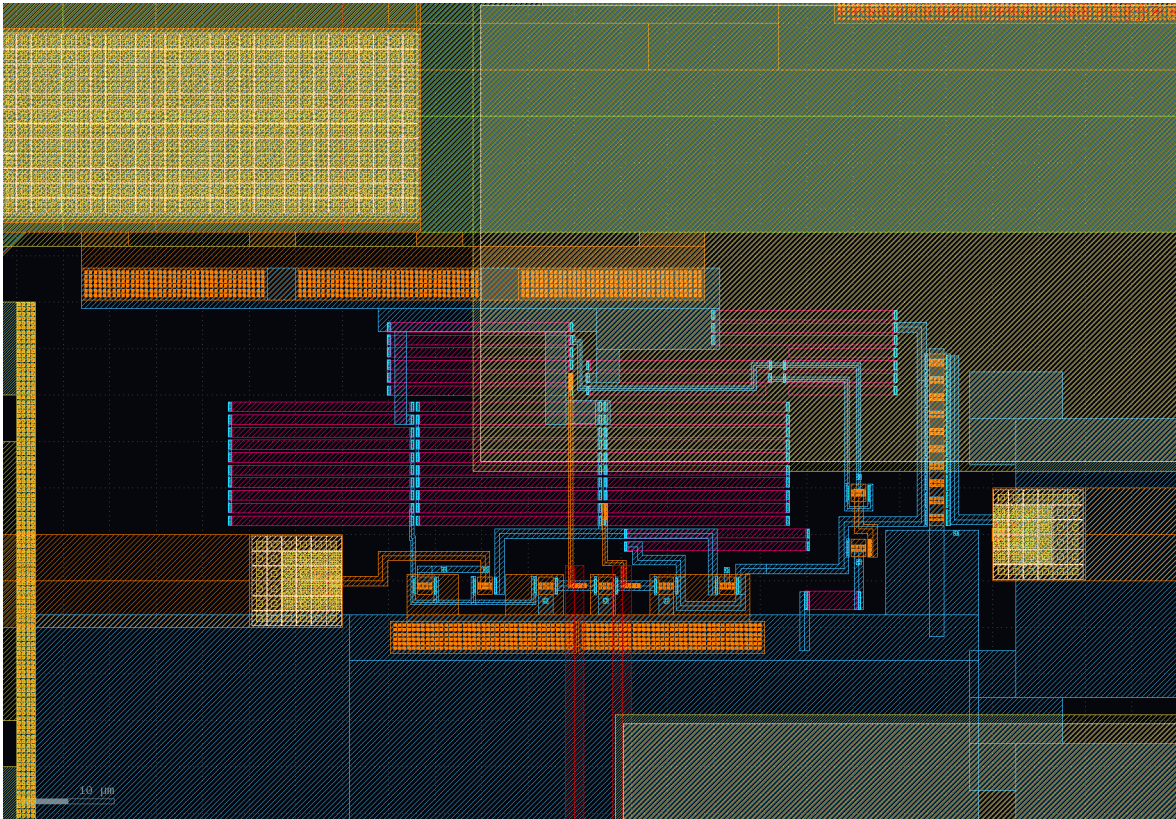
pin name	whats it
GND	supply and signal ground
SH_GND	shunt-anode, connect to GND, optional current measurement
3.3V	positive supply & shunt regulator cathode
ref	reference output & input. optional low-pass capacitor to GND
adj	adjust the band-gap-reference via resistor to 3.3V or GND
in	amplifier input
out	amplifier out
d-	differential amplifier inverting input
d+	differential amplifier non-inverting input
dout	differential amplifier laser diode output
dd-	double differential amplifier inverting input. connected together over two 500Ω
dd+	double differential amplifier non-inverting input. connected together over two 500Ω
ddout	double differential amplifier laser diode output

2.1 schematic



this single input amplifier ist DC-coupled and GND referenced. it drives a laser diode over Q1. its bias current is measured via Q8 and regulated from a norton amplifier build from Q11, Q7 and Q9. the low-pass-corner is set by R12 and C2 (that is also available over test-pads inside the power-ring of the chip). the RF-path goes over a base-circuit Q6 to Q10 and Q1. R3 is used to set the gain. Q2's job is to improve the temperature dependence of the bias-current.

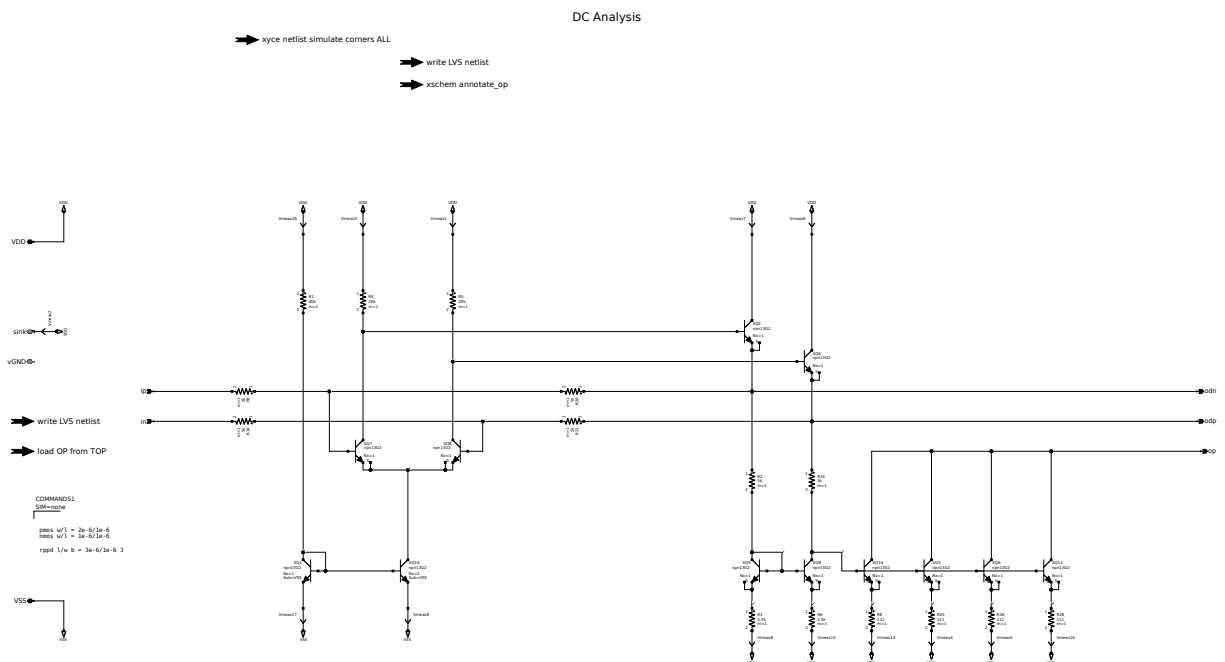
2.2 layout



the RPPD resistors are layout that way, because i had problems using LVS with resistors and was hoping it works with the simples shape. but in the end, i didn't manage to make LVS work anyway.

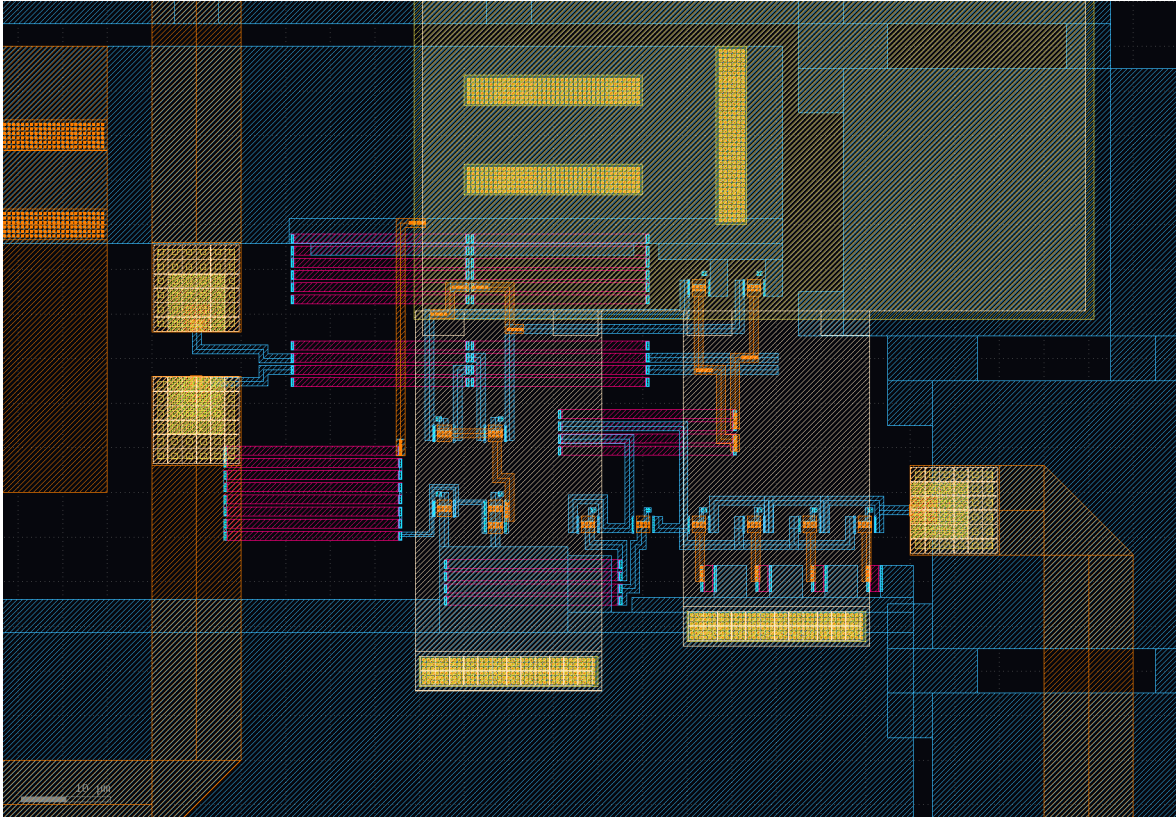
DIFFERENTIAL AMPLIFIER

3.1 schematic



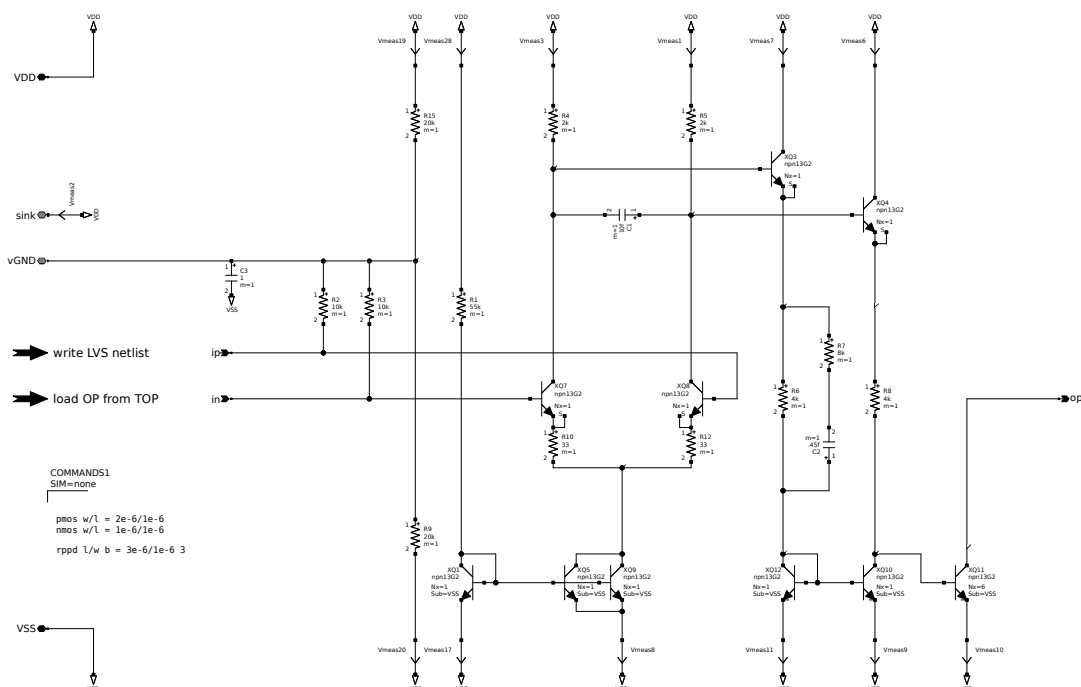
a simple voltage feedback (R9, R10 to R20, R21) differential amplifier, without common-mode-regulator. the output is converted over a current differencing amplifier (Q5, Q9 and Q14, Q3, Q6, Q11) to a single-ended signal.

3.2 layout



DUAL INPUT DIFFERENTIAL AMPLIFIER

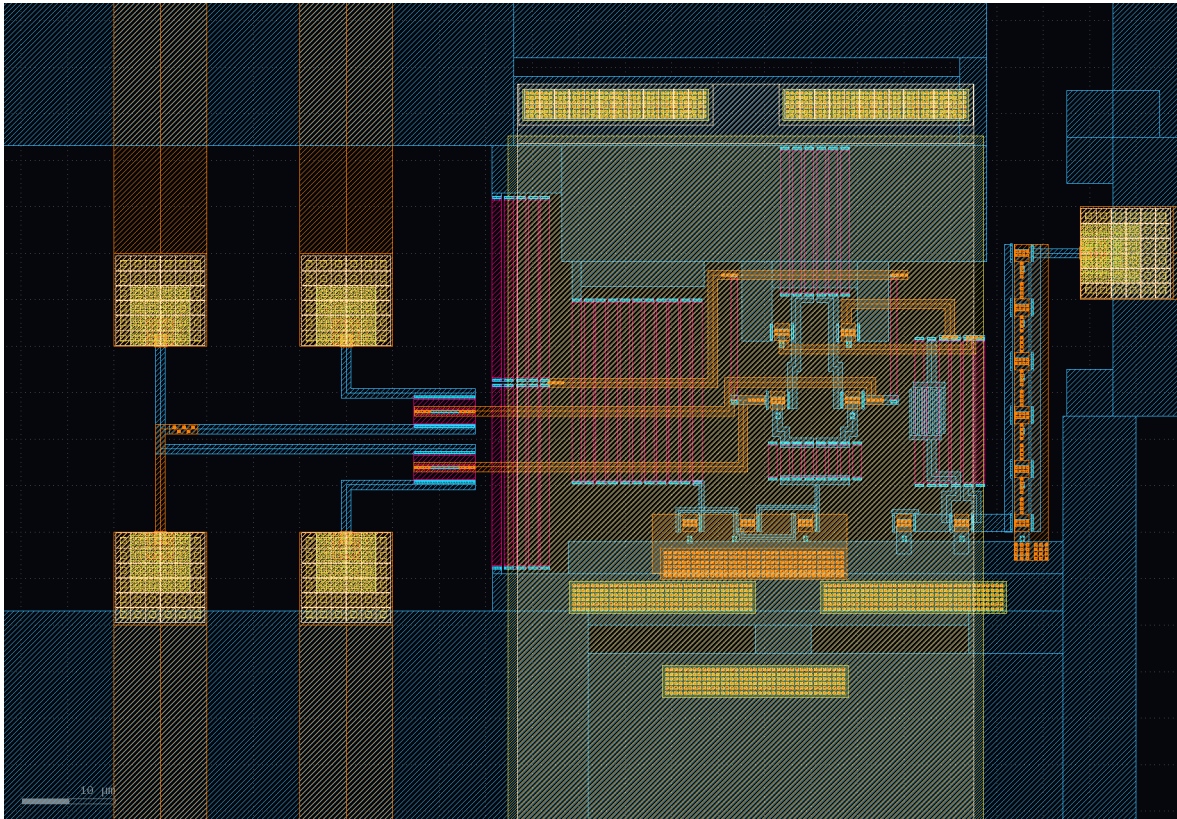
4.1 schematic



a simple current feedback (R10, R12) differential amplifier, without common-mode-regulator. the output is converted over a current differencing amplifier (Q12, Q10, Q11) to a single-ended signal.

the input ip is connected over two 500Ω resistors to both dd+ pads. the input in is connected over two 500Ω resistors to both dd- pads. its thought for compensation circuits that compensate capacitive coupled signals at the input.

4.2 layout



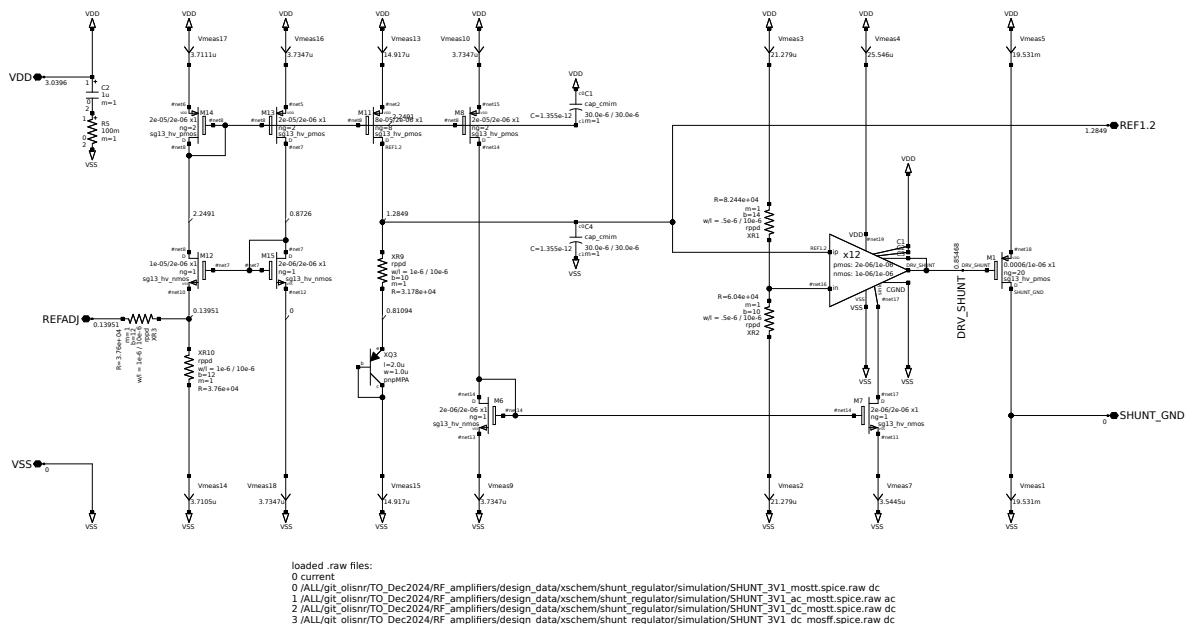
on the left side of the amplifier the for 500 Ω resistors are connected to the input-microstriplines.

AMPLIFIER SIMULATIONS

PDF with Xyce simulation

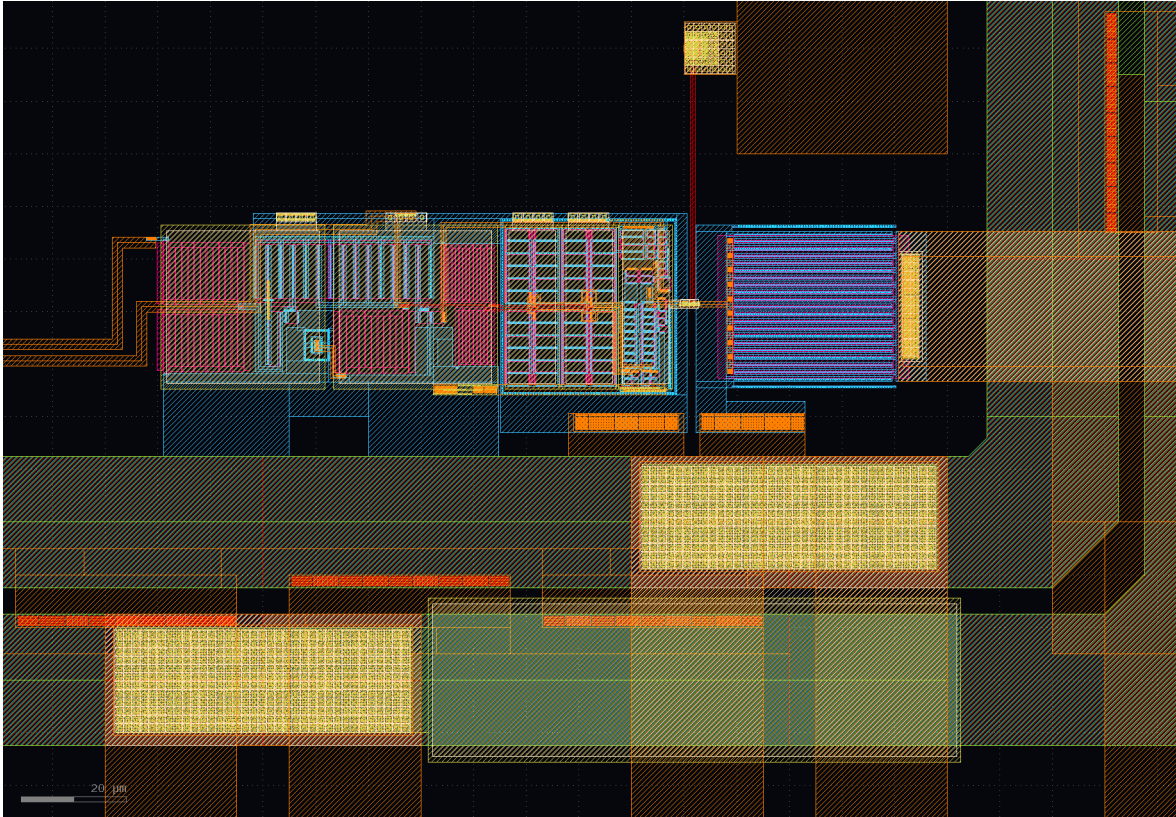
SHUNT REGULATOR 3.3V

6.1 schematic



this is a shunt-regulator for 3.3V and max. 50mA using a simple band-gap-reference. the reference uses MOSFET and BjT temperature coefficients, and needs only one BjT.

6.2 layout



6.3 options

there is the option to filter the reference output via a capacitor from the ref-pad to GND.

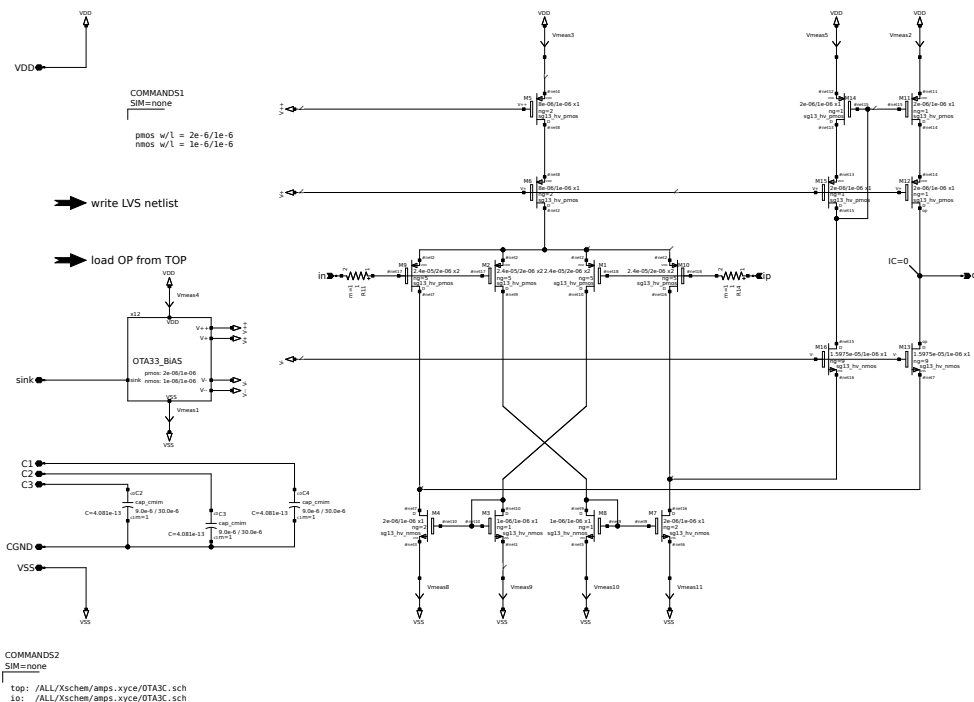
its also possible to adjust the temperature-turning-point via the adj-pad and the voltage via the ref pad.

6.4 simulation

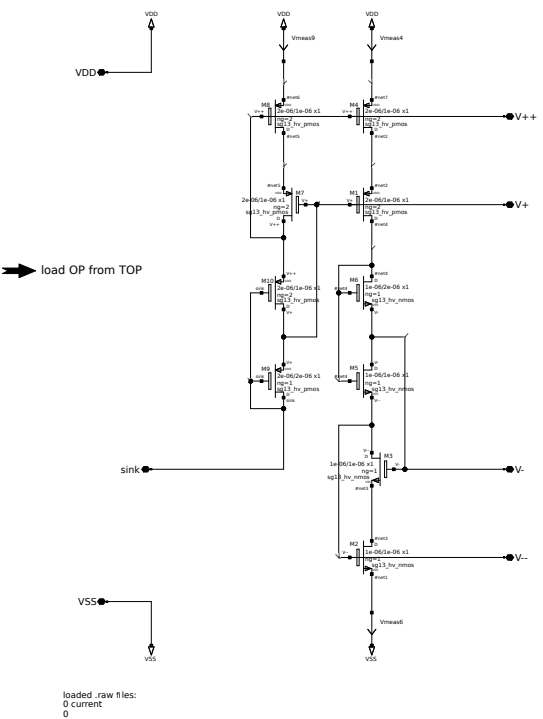
PDF with Xyce simulation

because of the used CMOS-process the PMOS transistors could have an isolated bulk, without special effort. the simulations showed that the isolated versions had a bigger gain, but a smaller common-mode-range, and i preferred the later. the bias-current is programmable an so also the band-width. the bias-voltages should allow wide-swing output voltages. in the space the circuit uses are 3 MiM-capacitors placed. they are intended to use for frequency-compensation or as power-rail decoupling.

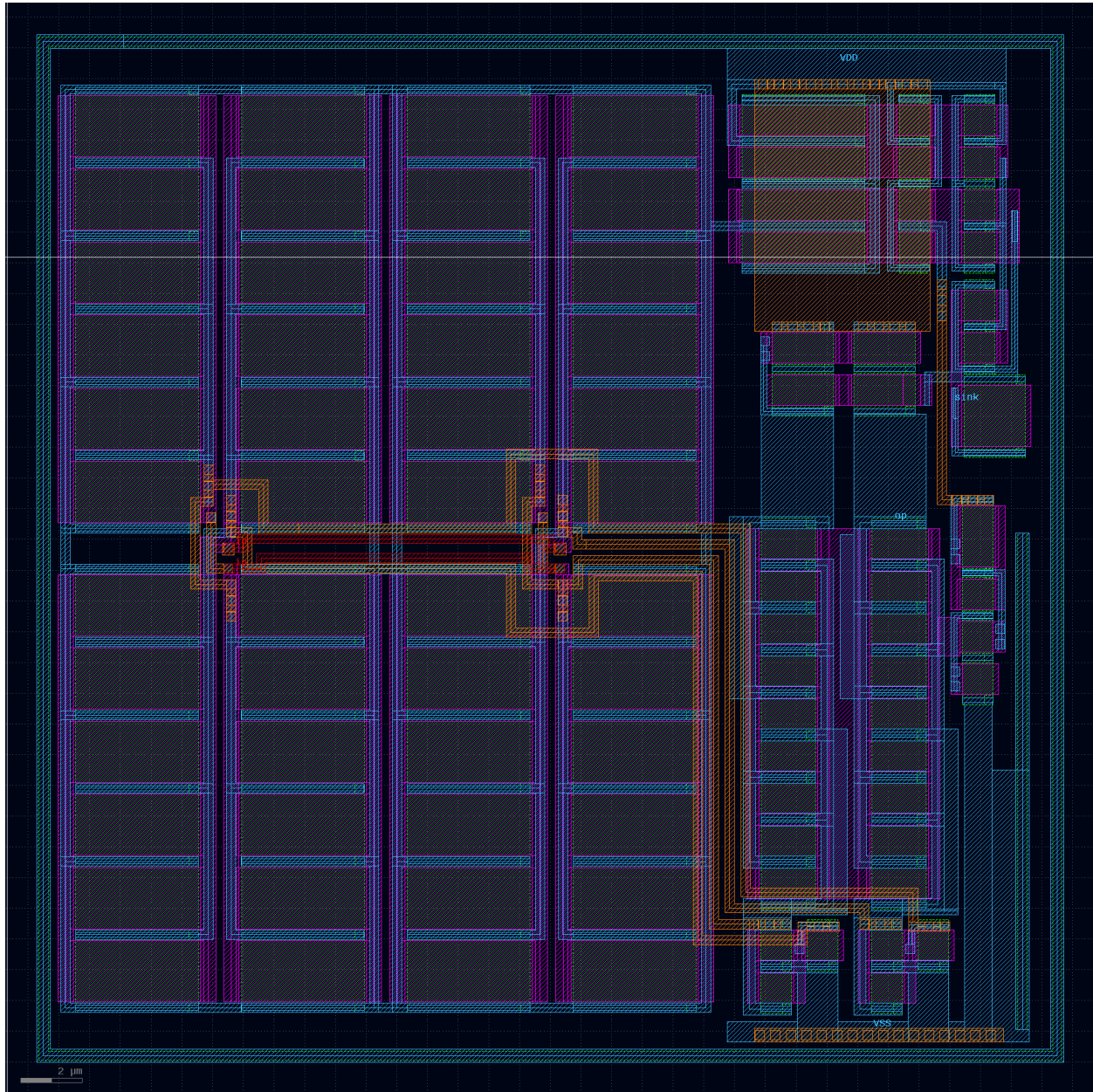
7.1 OTA



7.2 bias generator



7.3 layout



7.4 simulations

using different bias-currents of 1, 3 and 10 μ A a few simulations are printed into a PDF that allow to see the gain, common-mode-range, bandwidth and a slew-rate:

PDF with Xyce simulations `.ac` `.dc` `.trans`

the schematics of this simulations is Xschem document

7.5 ETHZ feedback

its a bit stupid to design OTAs that fit in a square, if there is no such space-requirement. the layout should be changed to minimize the conductor-length of the signals between the differential-stage and the current-mirrors.

EXPERIMENTS

8.1 RPPD



there are 6 resistors available to measure: 3 in X and Y orientations and both versions as dummy and normal resistors

8.2 sg13g2

there is a fast BjT for measurements.

8.3 calibration kit

to measure the amplifier impedances and to see the effect of pads and wire-bonding, there are an open, short and load calkit.

DESIGN DATA AND DESIGN PROCESS DESCRIPTION

9.1 iHP 130nm BiCMOS process sg13g2

the process is useable via iHPs openPDK:

source <https://github.com/IHP-GmbH/IHP-Open-PDK>

documentation <https://ihp-open-pdk-docs.readthedocs.io/en/latest/index.html>

open-source runs: <https://www.ihp-microelectronics.com/services/research-and-prototyping-service/fast-design-enablement/open-source-pdk>

9.2 Xschem schematics:

folder	for
design_data/xschem/OTA	design and simulation of the OTA
design_data/xschem/amplifiers	simulations of the three amplifiers
design_data/xschem/shunt_regulator	simulations of the voltage regulators
design_data/xschem/symbol	symbols for Xschem schematics

9.3 KLayout .GDS:

file	for
design_data/FMD_QNC_amps_filled.gds	layout of the chip

VALIDATION OF THE CIRCUITS

asap & subito...

Table of Contents

- *Three SiGe HBT amplifiers*